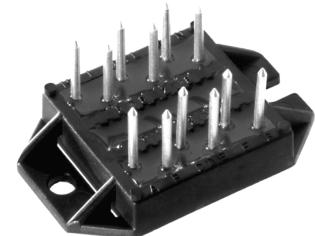
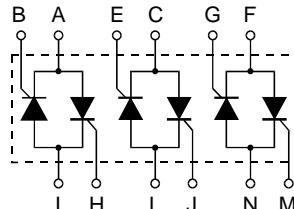


# AC Controller Modules

**I<sub>RMS</sub> = 3x 35 A**  
**V<sub>RRM</sub> = 600-1200 V**

Preliminary data

V <sub>RSM</sub>	V <sub>RRM</sub>	Type
V <sub>DSM</sub>	V <sub>DRM</sub>	
V	V	
700	600	VWO 35-06ho7
900	800	VWO 35-08ho7
1300	1200	VWO 35-12ho7



Symbol	Test Conditions	Maximum Ratings			Features
I <sub>RMS</sub>	T <sub>C</sub> = 85°C, (per phase)	35	A		
I <sub>TAVM</sub>	T <sub>C</sub> = 85°C; (180° sine ; per thyristor)	16	A		
I <sub>TSM</sub>	T <sub>VJ</sub> = 45°C; V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	200 210	A A	
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	180 190	A A	
I <sup>2</sup> t	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	200 150	A <sup>2</sup> s A <sup>2</sup> s	
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	160 150	A <sup>2</sup> s A <sup>2</sup> s	
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz, t <sub>p</sub> = 200 μs V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.15 A di <sub>G</sub> /dt = 0.15 A/μs	repetitive, I <sub>T</sub> = 20 A  non repetitive, I <sub>T</sub> = I <sub>TAVM</sub>	100 500	A/μs A/μs	
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GK</sub> = ∞; method 1 (linear voltage rise)	V <sub>DR</sub> = 2/3 V <sub>DRM</sub>	500	V/μs	
V <sub>RGM</sub>			10	V	
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> I <sub>T</sub> = I <sub>TAVM</sub>	t <sub>p</sub> = 30 μs t <sub>p</sub> = 300 μs	≤ 5 ≤ 2.5 0.5	W W W	
P <sub>GAVM</sub>			-40...+125	°C	
T <sub>VJ</sub>			125	°C	
T <sub>VJM</sub>			-40...+125	°C	
T <sub>stg</sub>			-40...+125	°C	
V <sub>ISOL</sub>	50/60 Hz, RMS I <sub>ISOL</sub> ≤ 1 mA	t = 1 min t = 1 s	2500 3000	V~ V~	
M <sub>d</sub>	Mounting torque (M4)		1.5 - 2 14 - 18	Nm lb.in.	
Weight	typ.		18	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.  
 IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values		
$I_D, I_R$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤	5	mA
$V_T$	$I_T = 20 \text{ A}; T_{VJ} = 25^\circ\text{C}$	≤	1.6	V
$V_{TO}$	For power-loss calculations only	0.85	V	
$r_T$		27	$\text{m}\Omega$	
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	≤	2.5	V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤	25	mA
	$T_{VJ} = -40^\circ\text{C}$	≤	50	mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤	0.2	V
$I_{GD}$		≤	3	mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	≤	75	mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	≤	50	mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.1 \text{ A}; di_G/dt = 0.1 \text{ A}/\mu\text{s}$	≤	2	$\mu\text{s}$
$R_{thJC}$	per thyristor; DC	1.3	K/W	
	per module	0.22	K/W	
$R_{thJK}$	per thyristor; DC	1.8	K/W	
	per module	0.3	K/W	
$d_s$	Creeping distance on surface	11.2	mm	
$d_A$	Creepage distance in air	5.0	mm	
$a$	Max. allowable acceleration	50	$\text{m}/\text{s}^2$	

## Dimensions in mm (1 mm = 0.0394")

